

TOSHIBA INSULATED GATE BIPOlar TRANSISTOR SILICON N-CHANNEL IGBT

# GT15Q101

HIGH POWER SWITCHING APPLICATIONS

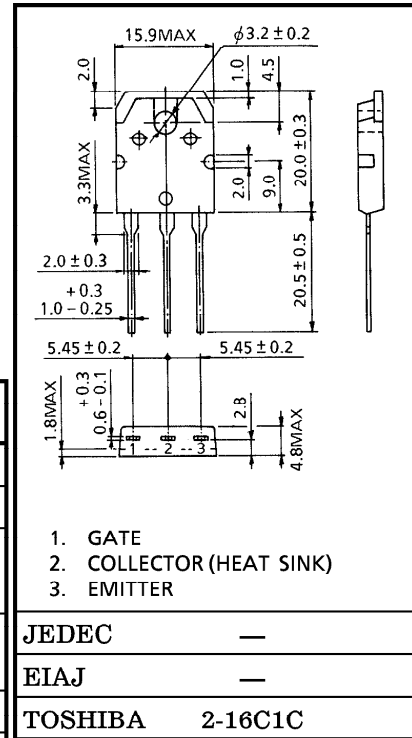
Unit in mm

MOTOR CONTROL APPLICATIONS

- High Input Impedance
- High Speed :  $t_f=0.5\mu s$  (Max.)
- Low Saturation Voltage :  $V_{CE(sat)}=4.0V$  (Max.)
- Enhancement-Mode

MAXIMUM RATINGS (Ta = 25°C)

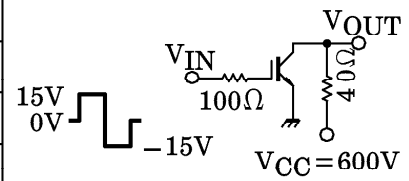
CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Emitter Voltage	$V_{CES}$	1200	V
Gate-Emitter Voltage	$V_{GES}$	$\pm 20$	V
Collector Current	DC	15	A
	1ms	30	
Collector Power Dissipation (Tc = 25°C)	$P_C$	150	W
Junction Temperature	$T_j$	150	°C
Storage Temperature Range	$T_{stg}$	-55~150	°C



Weight : 4.6g

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current	$I_{GES}$	$V_{GE} = \pm 20V, V_{CE} = 0$	—	—	$\pm 500$	nA
Collector Cut-off Current	$I_{CES}$	$V_{CE} = 1200V, V_{GE} = 0$	—	—	1.0	mA
Gate-Emitter Cut-off Voltage	$V_{GE(OFF)}$	$I_C = 15mA, V_{CE} = 5V$	3.0	—	6.0	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 15A, V_{GE} = 15V$	—	3.0	4.0	V
Input Capacitance	$C_{ies}$	$V_{CE} = 10V, V_{GE} = 0, f = 1MHz$	—	1800	—	pF
Switching Time	Rise Time	$t_r$	—	0.3	0.6	$\mu s$
	Turn-on Time	$t_{on}$	—	0.4	0.8	
	Fall Time	$t_f$	—	0.25	0.5	
	Turn-off Time	$t_{off}$	—	0.8	1.5	



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